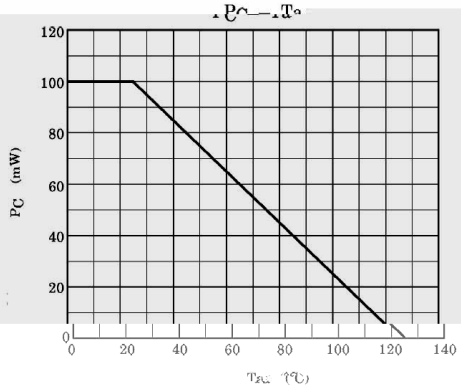
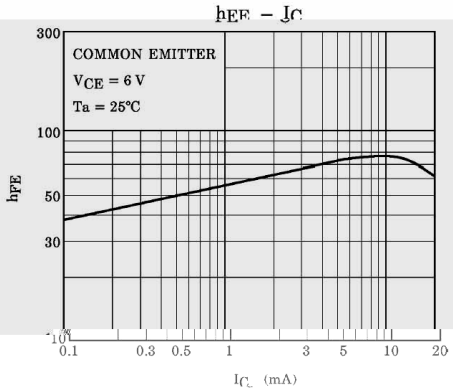
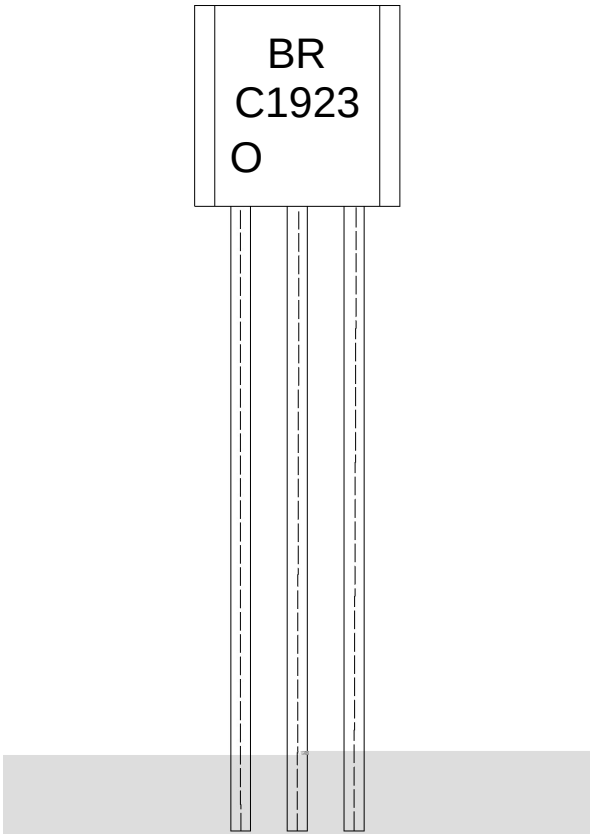
Silicon NPN transistor in a TO-92 Plastic Package.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	20	mA
Emitter Current - Continuous	I_E	-20	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=18V I_E=0			0.5	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			0.5	μA
DC Current Gain	h_{FE}	V_{CE}=6.0V I_C=1.0mA	40		200	
Transition Frequency	f_T	V_{CE}=6.0V I_C=1.0mA		550		MHz
Power Gain	G_{pe}	V_{CE}=6.0V I_E=-1.0mA f=100MHz	15	18		dB
Noise Figure	NF	V_{CE}=6.0V I_E=-1.0mA f=100MHz		2.5	5.0	dB
Collector- Base Time Constant	C_C.rbb′	V_{CE}=6.0V I_E=-1.0mA f=30MHz			30	ps
Common Emitter Reverse Transfer Capacitance	C_{re}	V_{CE}=6.0V f=1.0MHz		0.7		pF


120
100
80
60
40
20
0
PC (mW)
0
20
40
60
80
100
120
140


300
100
50
30
10
hFE
COMMON EMITTER
VCE = 6 V
Ta = 25°C
0.1
0.3
0.5
1
3
5
10
20
IC (mA)



Note:

BR:	Company Code.
C1923:	Product Type.
O:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

Note:

270 5 10 1 sec. Temp:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 ， 大箱